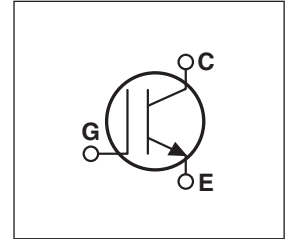
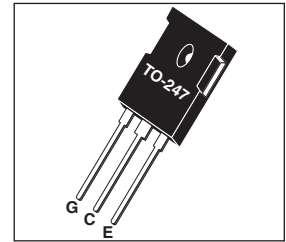


Utilizing the latest Field Stop and Trench Gate technologies, these IGBT's have ultra low  $V_{CE(ON)}$  and are ideal for low frequency applications that require absolute minimum conduction loss. Easy paralleling is a result of very tight parameter distribution and a slightly positive  $V_{CE(ON)}$  temperature coefficient. Low gate charge simplifies gate drive design and minimizes losses.

- 600V Field Stop
- Trench Gate: Low  $V_{CE(on)}$
- Easy Paralleling
- 6 $\mu$ s Short Circuit Capability
- 175°C Rated



**Applications: Welding, Inductive Heating, Solar Inverters, SMPS, Motor drives, UPS**

### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT50GN60B(G)	UNIT
$V_{CES}$	Collector-Emitter Voltage	600	Volts
$V_{GE}$	Gate-Emitter Voltage	$\pm 30$	
$I_{C1}$	Continuous Collector Current <sup>③</sup> @ $T_C = 25^\circ\text{C}$	107	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	64	
$I_{CM}$	Pulsed Collector Current <sup>①</sup> @ $T_C = 175^\circ\text{C}$	150	
SSOA	Switching Safe Operating Area @ $T_J = 175^\circ\text{C}$	150A @ 600V	
$P_D$	Total Power Dissipation	366	Watts
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 175	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 4mA$ )	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 800\mu A, T_J = 25^\circ\text{C}$ )	5.0	5.8	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 50A, T_J = 25^\circ\text{C}$ )	1.05	1.45	1.85	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 50A, T_J = 125^\circ\text{C}$ )		1.7		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_J = 25^\circ\text{C}$ ) <sup>②</sup>			25	$\mu A$
	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_J = 125^\circ\text{C}$ ) <sup>②</sup>			TBD	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			600	nA
$R_{G(int)}$	Intergrated Gate Resistor		N/A		$\Omega$



**CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

**DYNAMIC CHARACTERISTICS**
**APT50GN60B(G)**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	<b>Capacitance</b> $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		3200		pF	
$C_{oes}$	Output Capacitance			125			
$C_{res}$	Reverse Transfer Capacitance			100			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	Gate Charge		9.0		V	
$Q_g$	Total Gate Charge <sup>③</sup>	$V_{GE} = 15V$		325		nC	
$Q_{ge}$	Gate-Emitter Charge	$V_{CE} = 300V$		25			
$Q_{gc}$	Gate-Collector ("Miller") Charge	$I_C = 50A$		175			
SSOA	Switching Safe Operating Area	$T_J = 175^\circ\text{C}, R_G = 4.3\Omega^{\text{⑦}}, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 600V$	150			A	
SCSOA	Short Circuit Safe Operating Area	$V_{CC} = 360V, V_{GE} = 15V, T_J = 150^\circ\text{C}, R_G = 4.3\Omega^{\text{⑦}}$	6			$\mu\text{s}$	
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (25°C)</b>  $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 4.3\Omega^{\text{⑦}}$ $T_J = +25^\circ\text{C}$		20		ns	
$t_r$	Current Rise Time			25			
$t_{d(off)}$	Turn-off Delay Time			230			
$t_f$	Current Fall Time			100			
$E_{on1}$	Turn-on Switching Energy <sup>④</sup>				1185		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>⑤</sup>				1275		
$E_{off}$	Turn-off Switching Energy <sup>⑥</sup>				1565		
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (125°C)</b>  $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 4.3\Omega^{\text{⑦}}$ $T_J = +125^\circ\text{C}$		20		ns	
$t_r$	Current Rise Time			25			
$t_{d(off)}$	Turn-off Delay Time			260			
$t_f$	Current Fall Time			140			
$E_{on1}$	Turn-on Switching Energy <sup>④</sup>				1205		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>⑤</sup>				1850		
$E_{off}$	Turn-off Switching Energy <sup>⑥</sup>				2125		

**THERMAL AND MECHANICAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.41	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case (DIODE)			N/A	
$W_T$	Package Weight		5.9		gm

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages
- ③ See MIL-STD-750 Method 3471.
- ④  $E_{on1}$  is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.
- ⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)
- ⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)
- ⑦  $R_G$  is external gate resistance, not including  $R_{G(int)}$  nor gate driver impedance. (MIC4452)
- ⑧ Continuous current limited by package lead temperature.

APT Reserves the right to change, without notice, the specifications and information contained herein.

# TYPICAL PERFORMANCE CURVES

APT50GN60B(G)

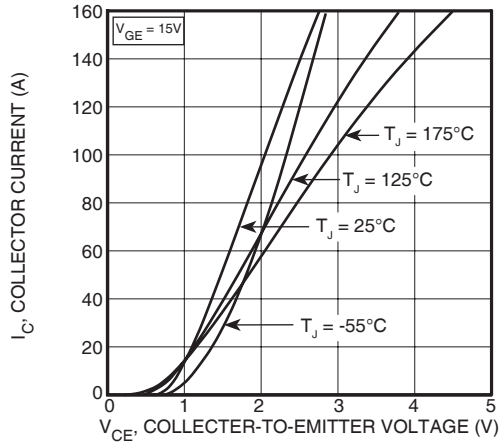


FIGURE 1, Output Characteristics ( $T_J = 25^\circ\text{C}$ )

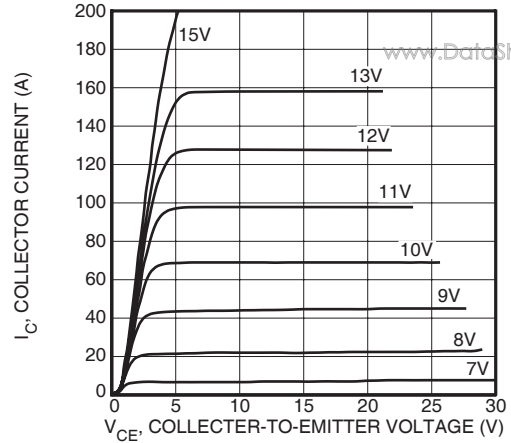


FIGURE 2, Output Characteristics ( $T_J = 125^\circ\text{C}$ )

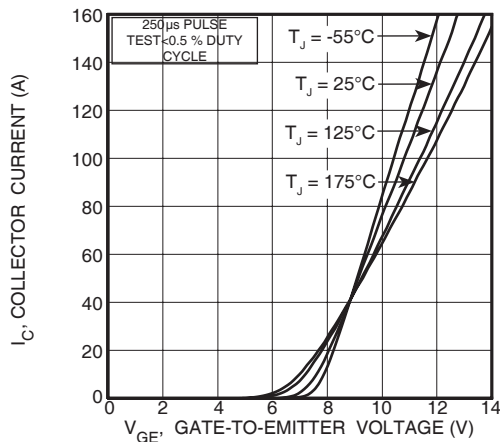


FIGURE 3, Transfer Characteristics

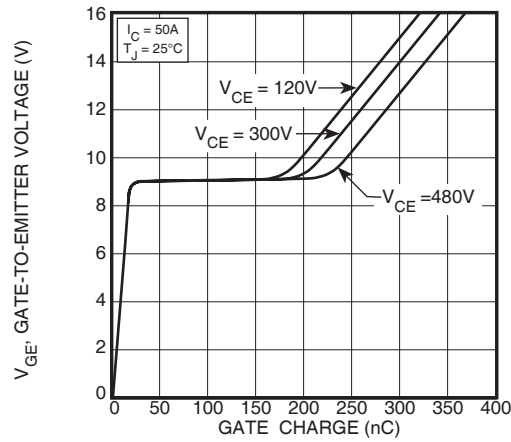


FIGURE 4, Gate Charge

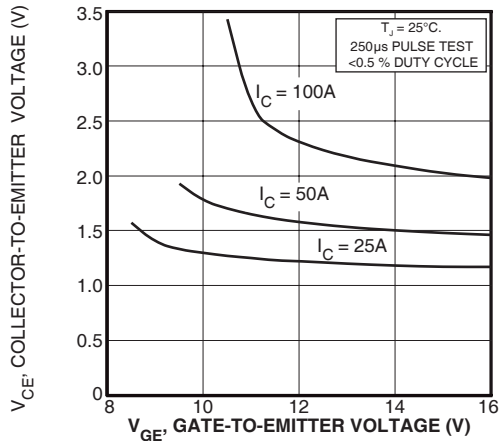


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

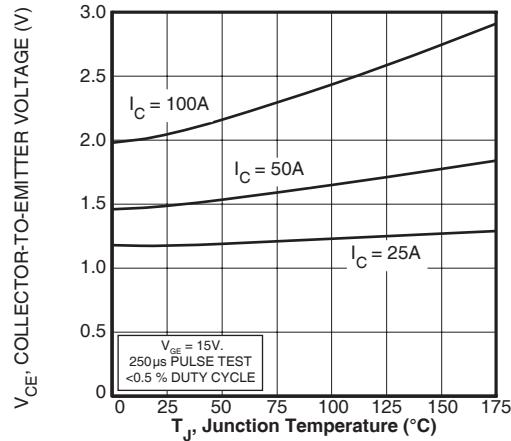


FIGURE 6, On State Voltage vs Junction Temperature

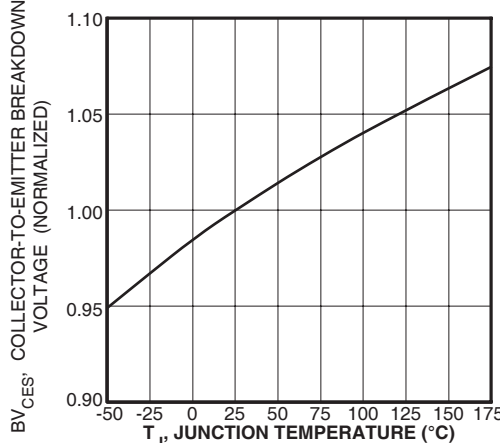


FIGURE 7, Breakdown Voltage vs. Junction Temperature

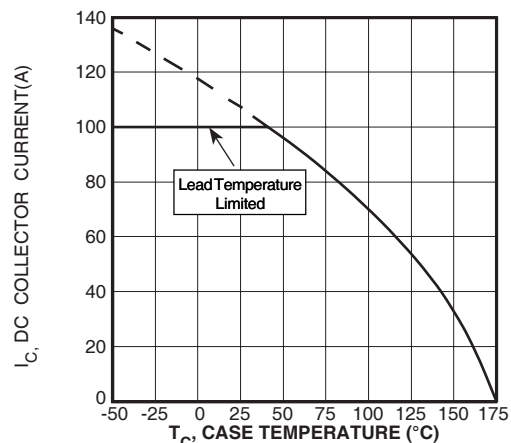


FIGURE 8, DC Collector Current vs Case Temperature

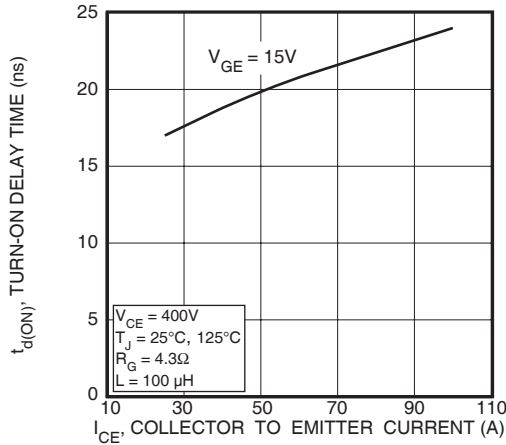


FIGURE 9, Turn-On Delay Time vs Collector Current

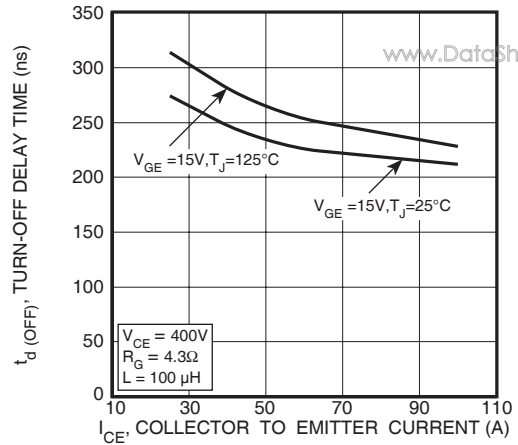


FIGURE 10, Turn-Off Delay Time vs Collector Current

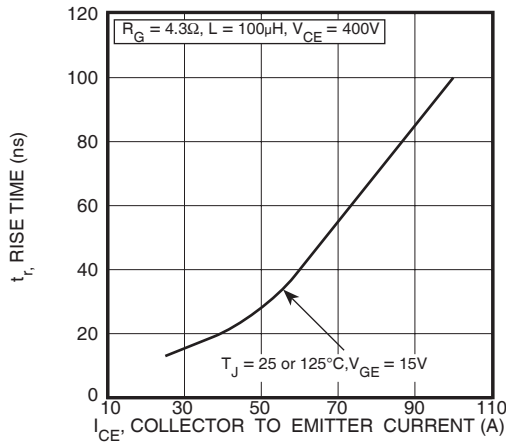


FIGURE 11, Current Rise Time vs Collector Current

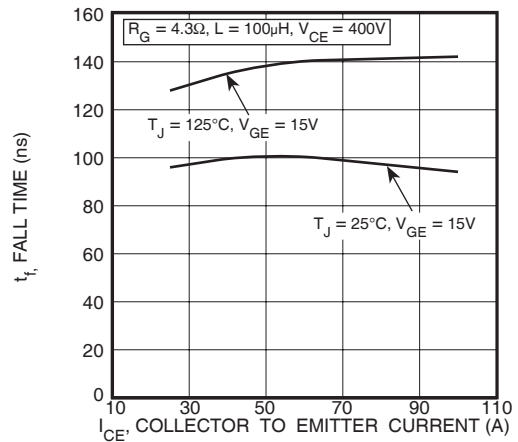


FIGURE 12, Current Fall Time vs Collector Current

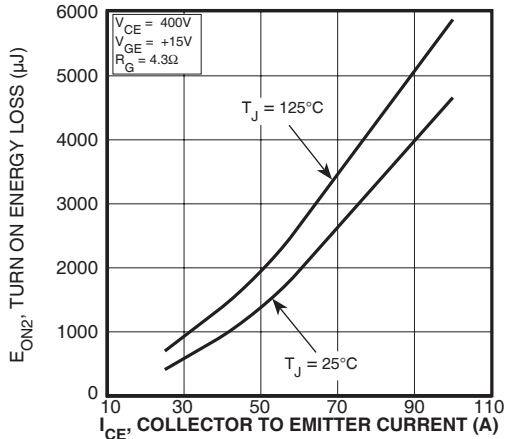


FIGURE 13, Turn-On Energy Loss vs Collector Current

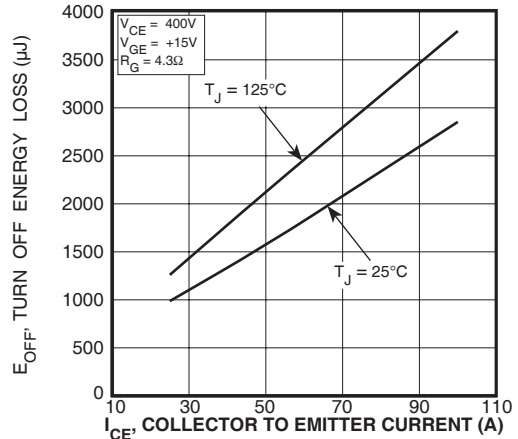


FIGURE 14, Turn Off Energy Loss vs Collector Current

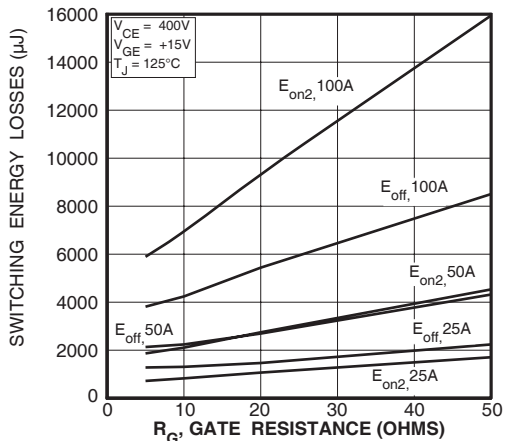


FIGURE 15, Switching Energy Losses vs. Gate Resistance

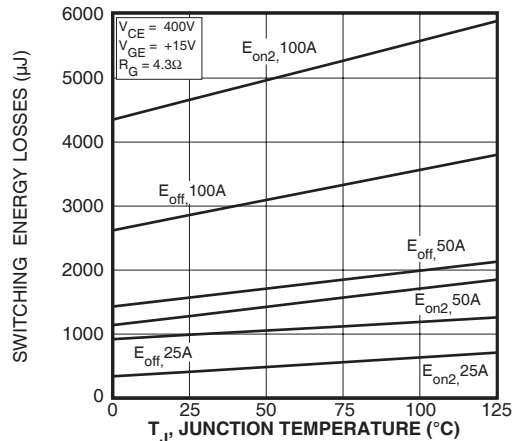


FIGURE 16, Switching Energy Losses vs Junction Temperature



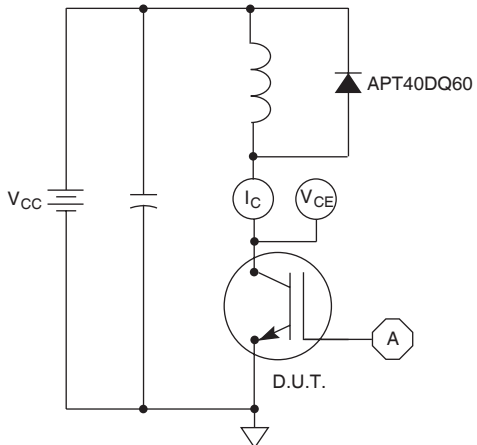


Figure 21, Inductive Switching Test Circuit

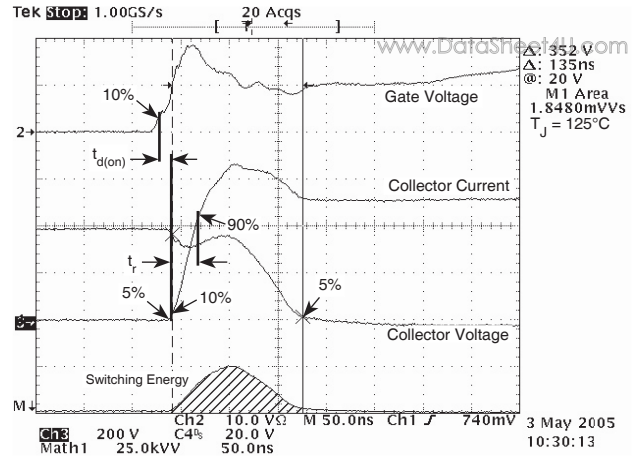


Figure 22, Turn-on Switching Waveforms and Definitions

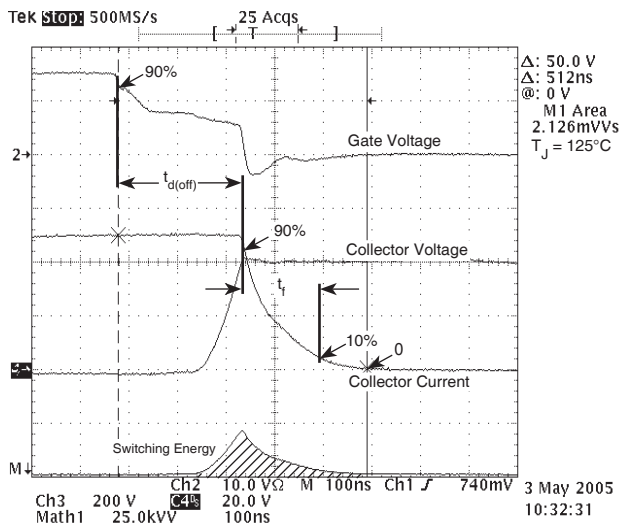
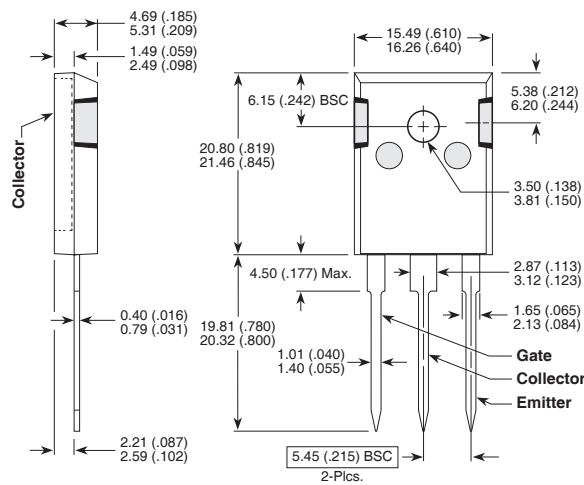


Figure 23, Turn-off Switching Waveforms and Definitions

TO-247 Package Outline

ⓔ1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)